

219302US-2 CONT

Handwritten notes: #4/A, 7/19/12, DS

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
KAZUO TOMITA ET AL : ATTN: APPLICATION DIVISION
SERIAL NO: NEW U.S. APPLICATION :
FILED: HEREWITH :
FOR: SEMICONDUCTOR DEVICE AND
METHOD OF MANUFACTURING
THE SAME

PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Prior to a first examination on the merits, please amend the above-identified application as follows:

IN THE TITLE

Please delete the original title and insert therefor:

SEMICONDUCTOR DEVICE WITH AN IMPROVEMENT IN
ALIGNMENT, AND METHOD OF MANUFACTURING THE SAME

IN THE SPECIFICATION

Please replace the paragraph at page 4, lines 2-4, with the following text:

The interlayer insulating film 107 is also formed in the element formation region SR,
and on the interlayer insulating film 107 planarized by CMP, the bit line layer 109 is formed.

A2

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